

YJ Planar Schottky Barrier Diode Die Specification

60V 2A, 45mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB045S060SS-280A

Main Products Characteristics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)			
Parameter	Symbol	Rating	Parameter	Symbol	Value	
					Spec	Typical
Repetitive peak reverse voltage	V _{RRM}	60 V	Reverse breakdown voltage	V _{BR}	65 V	72V
Average forward current	I _{F(AV)}	2 A	I _R = 1mA			
(tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	50 A	I _F = 2 A	V _F		
Storage temperature range	T _{stg}	-50 to +175 °C				
Maximum operating junction temperature	T _j	175 °C	Maximum reverse current			
			V _R = V _{RRM}	I _R	10uA	2uA

Device Schematics and Outline Drawing

Die Thickness *	
Die Size **	45 Mils
Top Metal Pad	40 Mils
Active Area	36 Mils
Top Metal	Ag
Back Metal	Ag
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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